

<b>Notice of References Cited</b>	Application/Control No. 09/974,814	Applicant(s)/Patent Under Reexamination SAHARA ET AL.	
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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-			
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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